XN01504 (XN1504)

Silicon NPN epitaxial planar type

For amplification of low-frequency output

■ Features

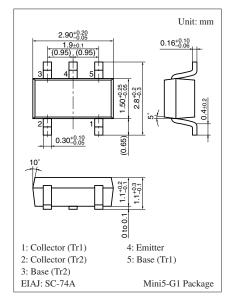
- Two elements incorporated into one package (Emitter-coupled transistors)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

• 2SD1915F × 2

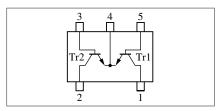
■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	50	V	
Collector-emitter voltage (Base open)	V _{CEO}	20	V	
Emitter-base voltage (Collector open)	V_{EBO}	25	V	
Collector current	I_C	300	mA	
Peak collector current	I_{CP}	500	mA	
Total power dissipation	P_{T}	300	mW	
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



Marking Symbol: 5S

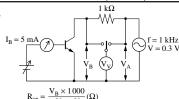
Internal Connection



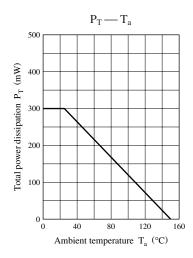
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

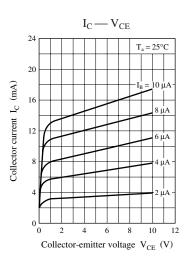
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Base-emitter voltage	V_{BE}	$V_{CE} = 2 \text{ V}, I_{C} = 4 \text{ mA}$		0.6		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$			0.1	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 25 \text{ V}, I_{C} = 0$			0.1	μA
Forward current transfer ratio	h _{FE}	$V_{CE} = 2 \text{ V}, I_{C} = 4 \text{ mA}$	500		2500	_
h _{FE} ratio *1	h _{FE(Small}	$V_{CE} = 2 \text{ V}, I_{C} = 4 \text{ mA}$	0.50	0.99		_
	/Large)					
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 30 \text{ mA}, I_B = 3 \text{ mA}$			0.1	V
Transition frequency	f_T	$V_{CB} = 6 \text{ V}, I_E = -4 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			7	pF
(Common base, input open circuited)						
ON resistanse *2	R _{on}			1.0		Ω

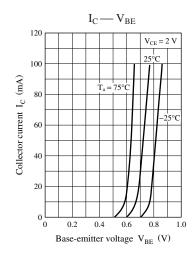
- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
 - 2. *1: Ratio between 2 elements
 - *2: Ron start resistance test circuit

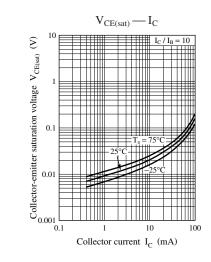


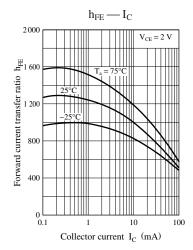
 $R_{on} = \frac{V_B \times 1000}{V_A - V_B}(\Omega)$ Note) The part number in the parenthesis shows conventional part number.

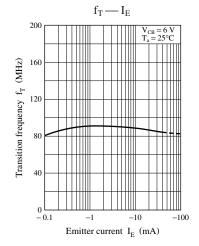


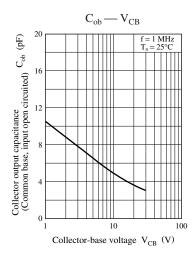












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